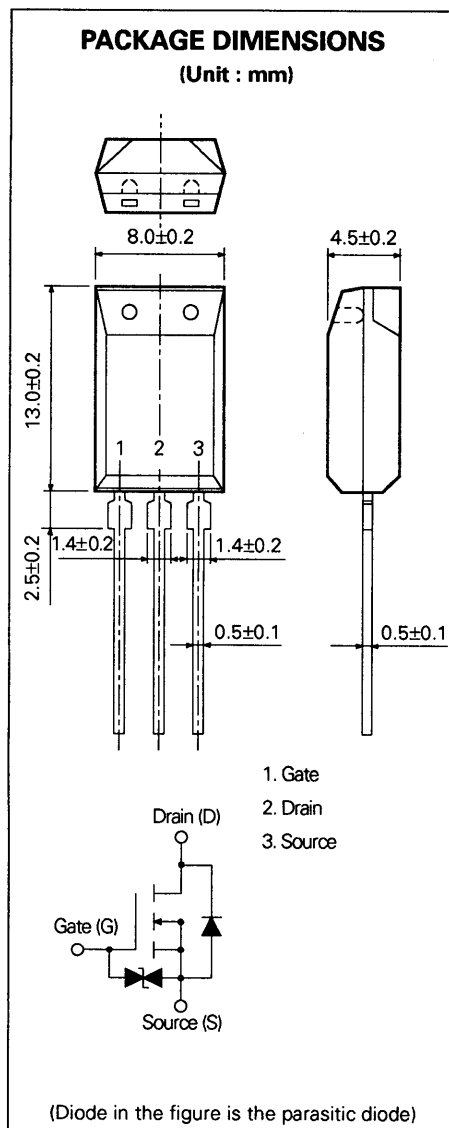


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P1 98.2

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE



DESCRIPTION

The 2SK2132 is N-channel Power MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-state Resistance
 $R_{DS(on)} = 0.65 \Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 2.0 \text{ A)}$
- Low C_{iss} $C_{iss} = 300 \text{ pF TYP.}$
- Built-in G-S Gate Protection Diodes
- High Avalanche Capability Ratings

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature	-55 to +150	°C
Channel Temperature	150	°C MAX.

Maximum Power Dissipation

Total Power Dissipation ($T_a = 25 \text{ }^\circ\text{C}$)	1.8	W
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Maximum Voltages and Currents ($T_a = 25 \text{ }^\circ\text{C}$)

V_{DSS}	Drain to Source Voltage	180	V
V_{GSS}	Gate to Source Voltage	± 20	V
$I_{D(DC)}$	Drain Current (DC)	± 4.0	A
$I_{D(pulse)^*}$	Drain Current (pulse)	± 16	A

Maximum Avalanche Capability Ratings**

I_{AS}	Single Avalanche Current	4.0	A
EAS	Single Avalanche Energy	51.2	mJ

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

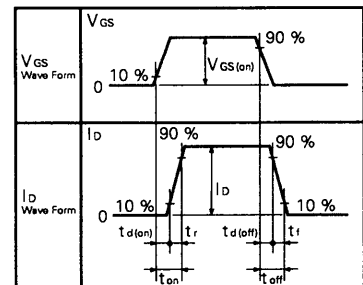
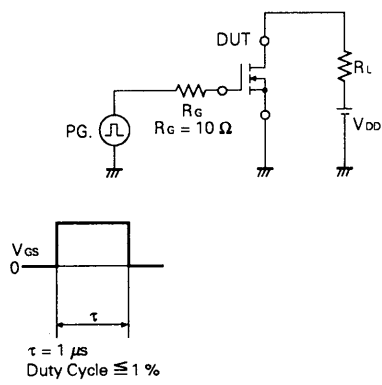
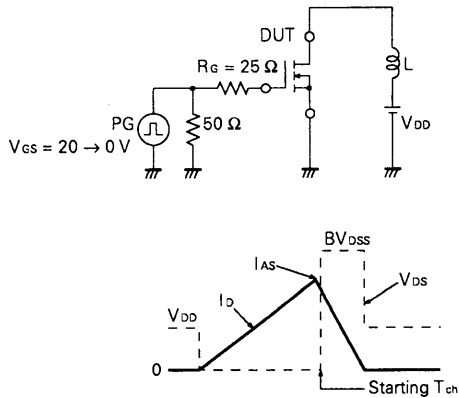
** Starting $T_{ch} = 25 \text{ }^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0$

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

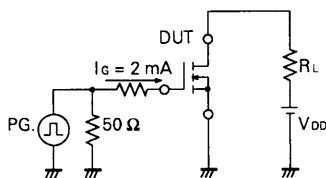
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance	R _{DS (on)}		0.52	0.65	Ω	V _{GS} = 10 V, I _D = 18 A
Gate to Source Cutoff Voltage	V _{GS (off)}	2.0		4.0	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	y _{fs}	0.5			S	V _{DS} = 10 V, I _D = 18 A
Drain Leakage Current	I _{DSS}			100	μA	V _{DS} = 500 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±20 V, V _{DS} = 0
Input Capacitance	C _{iss}		300		pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output Capacitance	C _{oss}		170		pF	
Reverse Transfer Capacitance	C _{rss}		50		pF	
Turn-On Delay Time	t _{d (on)}		9.0		ns	V _{GS} = 10 V V _{DD} = 100 V I _D = 2 A, R _G = 10 Ω R _L = 50 Ω
Rise Time	t _r		10		ns	
Turn-Off Delay Time	t _{d (off)}		28		ns	
Fall Time	t _f		12		ns	
Total Gate Charge	Q _G		10		nC	V _{GS} = 10 V I _D = 2 A V _{DD} = 140 V
Gate to Source Charge	Q _{GS}		2.3		nC	
Gate to Drain Charge	Q _{GD}		4.7		nC	
Diode Forward Voltage	V _{F(S-D)}		0.9		V	I _F = 2 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		180		ns	I _F = 2 A
Reverse Recovery Charge	Q _{rr}		0.5		μC	di / dt = 50 A/μs

Test Circuit 1 : Avalanche Capability

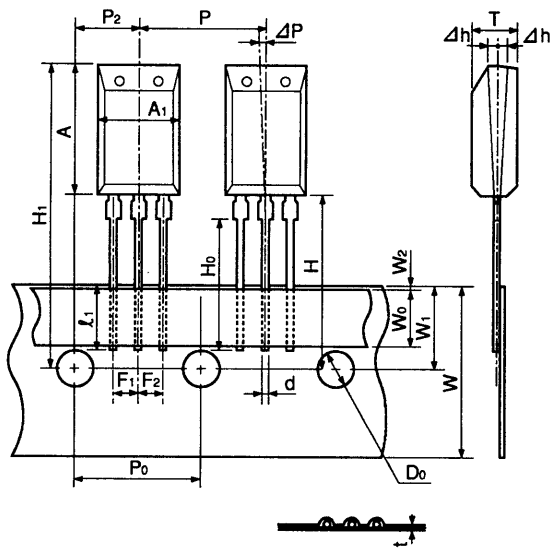
Test Circuit 2 : Switching Time



Test Circuit 3 : Gate Charge



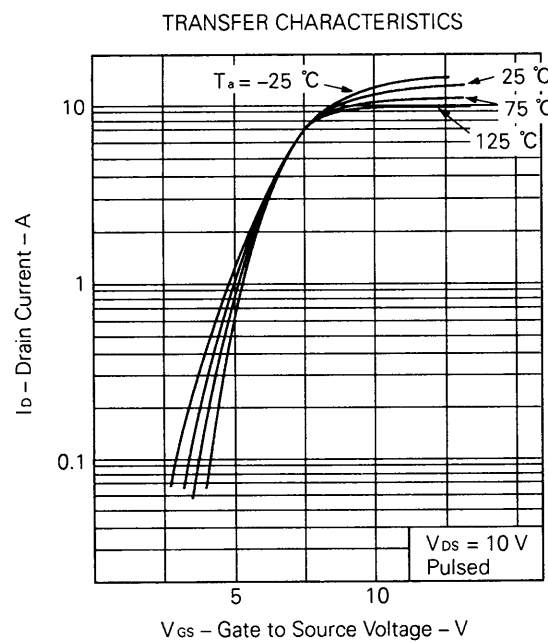
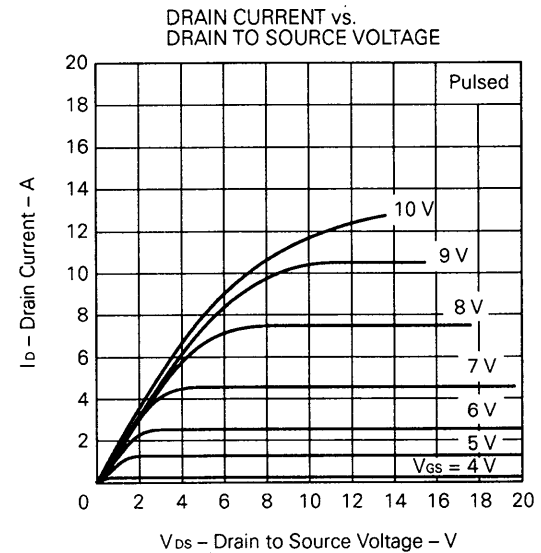
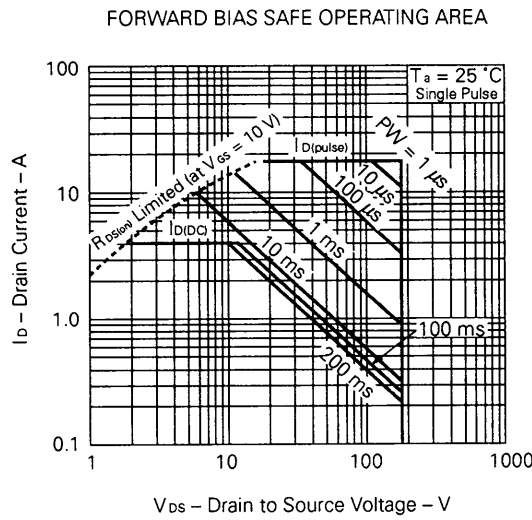
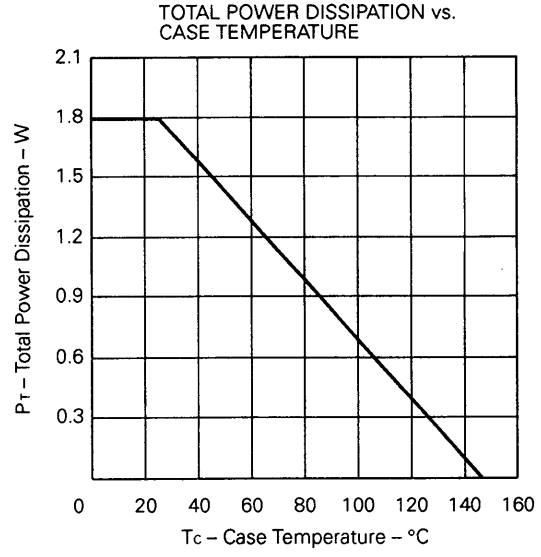
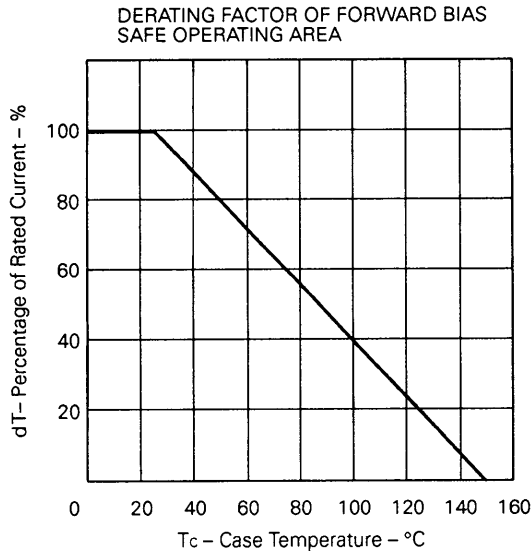
Radial Tape Specification



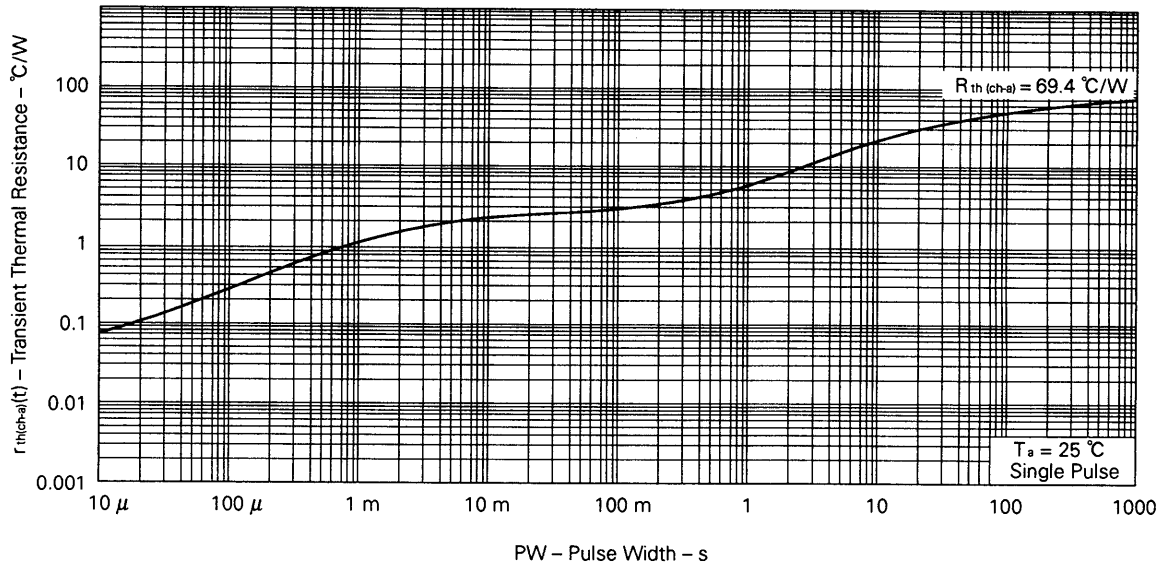
Dimension (unit : mm)

Item		
Component Body Length along Tape	A_1	8.0 ± 0.2
Component Body Height	A	13.0 ± 0.2
Component Body Width	T	4.5 ± 0.2
Component Lead Width Dimension	d	0.5 ± 0.1
Lead Wire Enclosure	l_1	2.5 MIN.
Component Center Pitch	P	12.7 ± 1.0
Feedhole Pitch	P_0	12.7 ± 0.3
Feedhole Center to Center Lead	P_2	6.35 ± 0.5
Component Lead Pitch	F_1, F_2	$2.5 \begin{matrix} + 0.4 \\ - 0.1 \end{matrix}$
Deflection Front or Rear	Δh	± 1.0
Deflection Left or Right	ΔP	± 1.3
Carrier Strip Width	W	$18.0 \begin{matrix} + 1.0 \\ - 0.5 \end{matrix}$
Adhesive Tape Width	W_0	5.0 MIN.
Feedhole Location	W_1	9.0 ± 0.5
Adhesive Tape Position	W_2	0.7 MIN.
Height of Seating Plane	H_0	16.0 ± 0.5
Feedhole to upper of Component	H_1	32.2 MAX.
Feedhole to Bottom of Component	H	20.0 MAX.
Tape Feedhole Diameter	D_0	4.0 ± 0.2
Overall Taped Package Thickness	t	0.7 ± 0.2

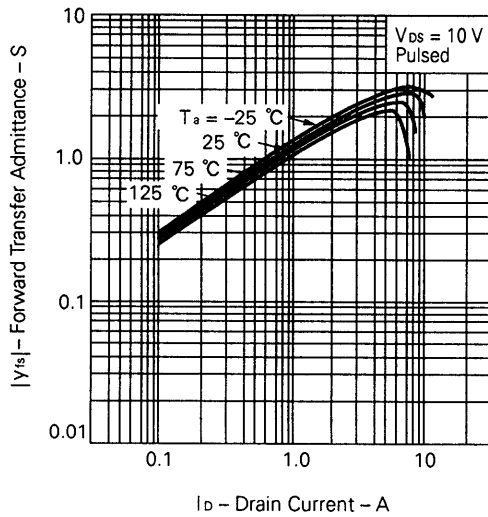
TYPICAL CHARACTERISTICS (T_a = 25 °C)



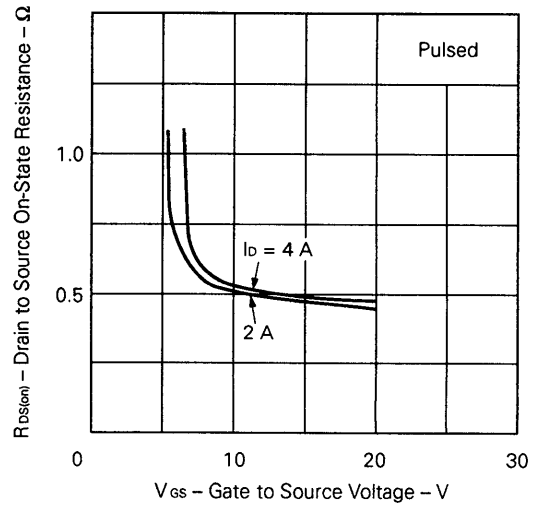
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



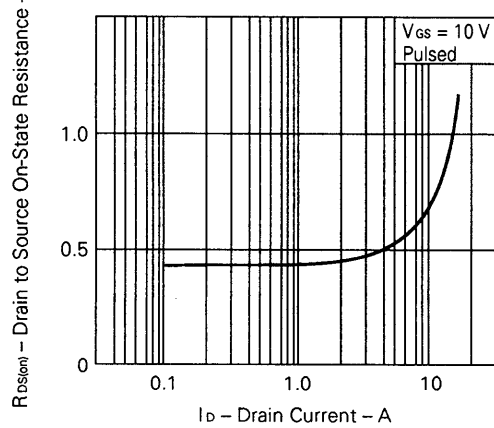
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



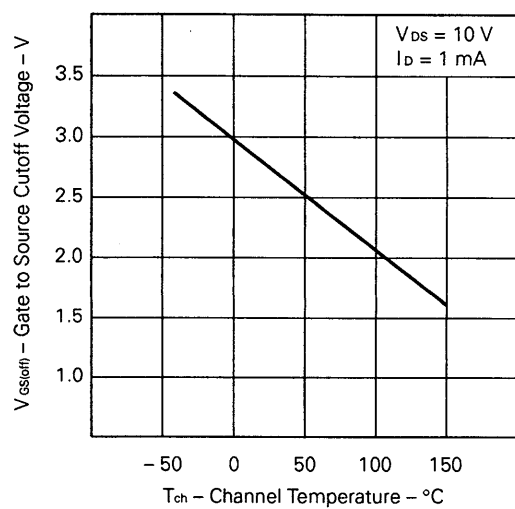
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



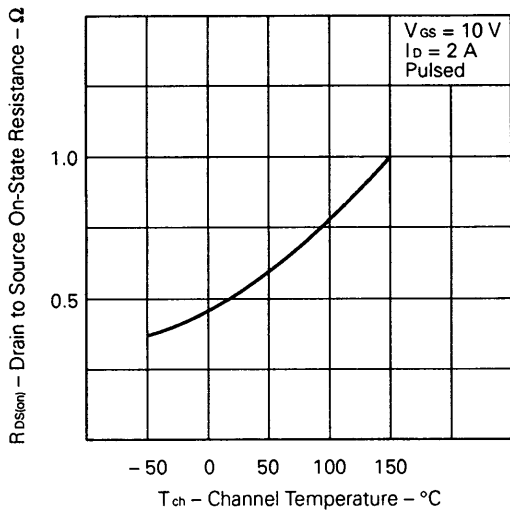
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



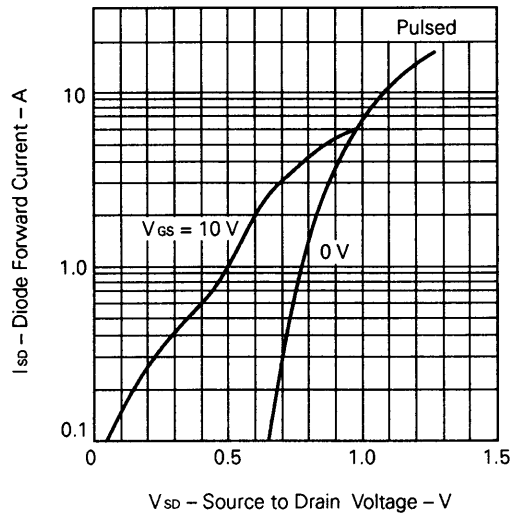
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



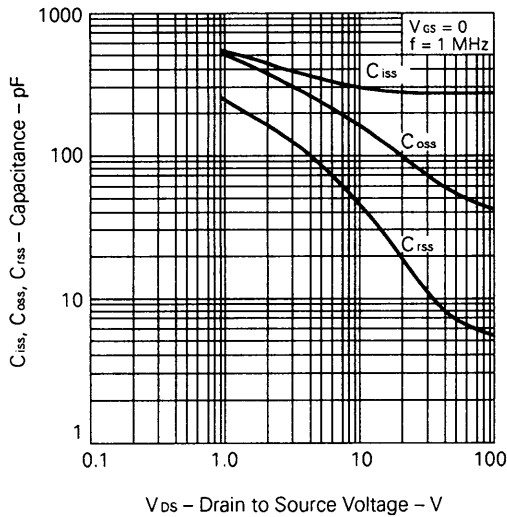
DRAIN TO SOURCE ON - STATE RESISTANCE vs. CHANNEL TEMPERATURE



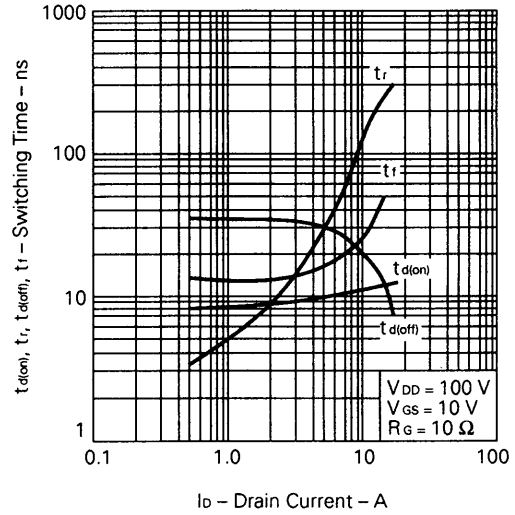
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



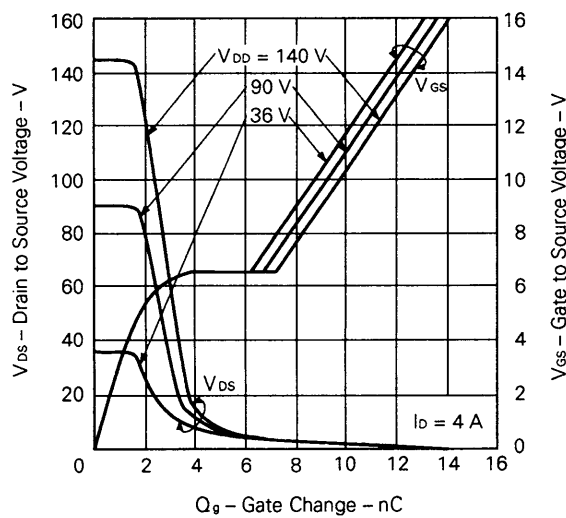
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



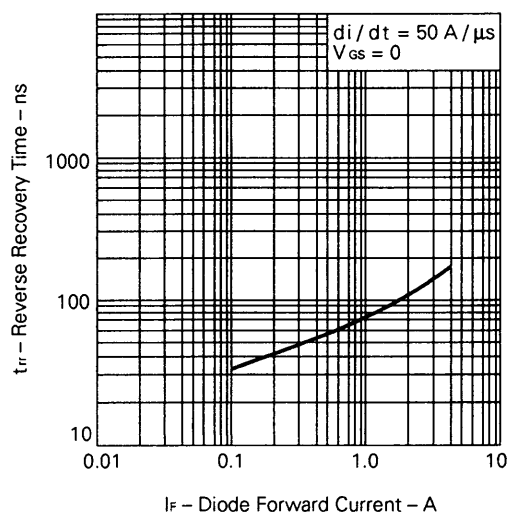
SWITCHING CHARACTERISTICS



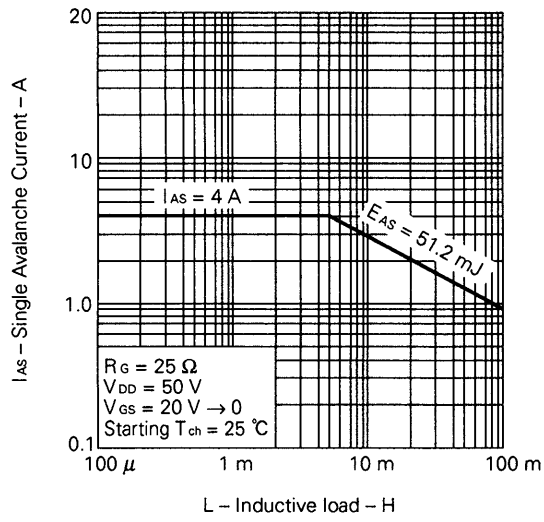
DYNAMIC INPUT CHARACTERISTICS



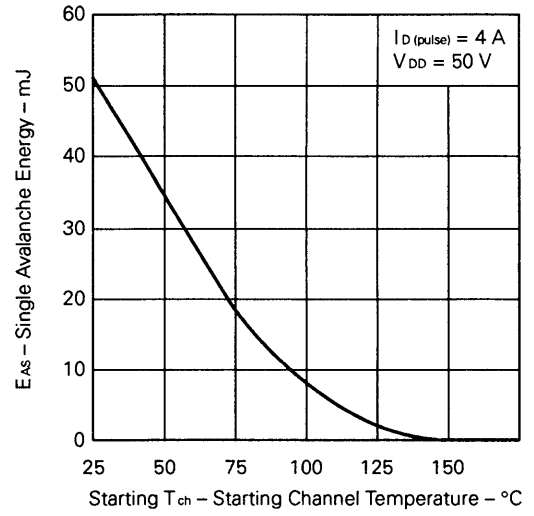
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCE CURRENT vs. INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY vs. STARTING CHANNEL TEMPERATURE



[MEMO]

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